TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

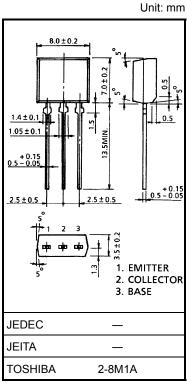
# 2SA1892

# Power Amplifier Applications Power Switching Applications

- Low collector-emitter saturation voltage: VCE (sat) = -0.5 V (max) (IC = -1 A, IB = -0.05 A)
- High collector power dissipation: PC = 1.3 W
- High-speed switching time:  $t_{stg} = 1.0 \mu s$  (typ.)
- Complementary to 2SC5029

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	-50	V
Collector-emitter voltage	V <sub>CEO</sub>	-50	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	IC	-3	Α
Base current	lΒ	-0.2	Α
Collector power dissipation	PC	1.3	W
Junction temperature	Tj	150	°C
Storage temperature range	T <sub>stg</sub>	-55 to 150	°C



Weight: 0.55 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

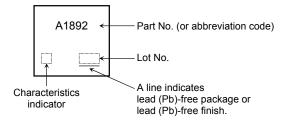


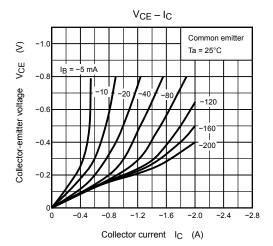
## **Electrical Characteristics (Ta = 25°C)**

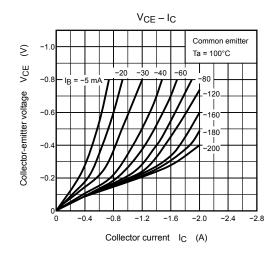
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off c	urrent	I <sub>CBO</sub>	V <sub>CB</sub> = -50 V, I <sub>E</sub> = 0	_	_	-1.0	μΑ
Emitter cut-off cur	rent	I <sub>EBO</sub>	V <sub>EB</sub> = -5 V, I <sub>C</sub> = 0	_	_	-1.0	μΑ
Collector-emitter I	breakdown voltage	V (BR) CEO	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-50	_	_	V
DC current gain		h <sub>FE (1)</sub> (Note)	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	70	_	240	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = -2 V, I <sub>B</sub> = -1.5 A	40	_	_	
Collector-emitter	saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -1 A, I <sub>B</sub> = -0.05 A	_	_	-0.5	V
Base-emitter satu	ration voltage	V <sub>BE (sat)</sub>	I <sub>C</sub> = -1 A, I <sub>B</sub> = -0.05 A	_	_	-1.2	V
Transition frequency		f <sub>T</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	_	100	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	40	_	pF
Switching time	Turn-on time	t <sub>on</sub>	Output  20 $\mu$ s Input $\stackrel{B2}{\longrightarrow}$ $\stackrel{C}{\longrightarrow}$	_	0.1	_	
	Storage time	t <sub>stg</sub>		_	1.0	_	μs
	Fall time	t <sub>f</sub>		_	0.1	_	

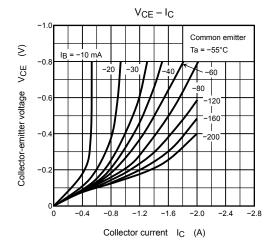
Note: hFE (1) classification O: 70 to 140, Y: 120 to 240

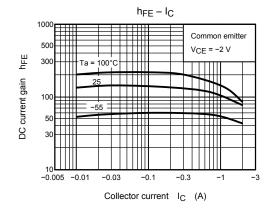
## Marking

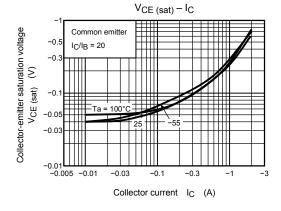


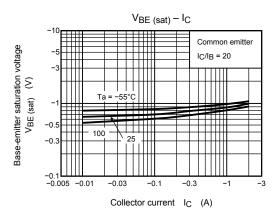




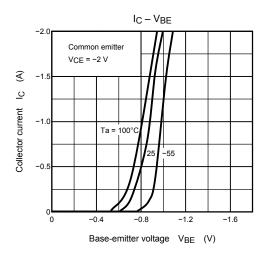


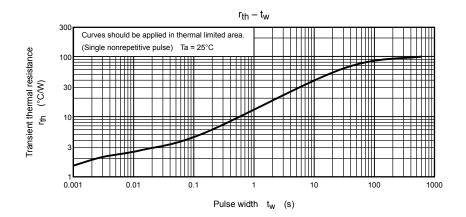


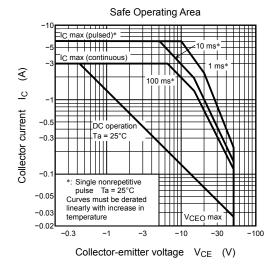


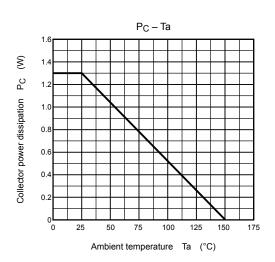


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